WEJ®

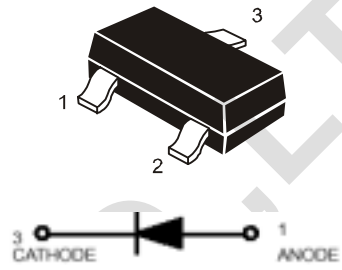
RoHS

BAS116LT1

SURFACE MOUNT SWITCHING DIODE

- Low Leakage Current Applications
- Medium Speed Switching Times

Package:SOT-23



ABSOLUTE MAXIMUM RATINGS at Ta=25℃

Characteristic	Symbol	Rating	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Peak Repetitive Reverse Voltage working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	75	V
Peak Forward Current	I_F	200	mAdc
Forward Continuous Current(Note)	I_{FM}	300	mAdc
Power Dissipation (Note) Derate Above 25℃	P_D	300 2.4	mW mW/℃
Junction Temperature	Tj	150	℃
Storage Temperature	Tstg	-50-150	℃

Note:Diode Ceramic Substrate 10mm x 8.0mm x 0.7mm

ELECTRICAL CHARACTERISTICS at Ta=25℃

Characteristic	Symbol	Min	Max	Unit	Test Conditions
Forward Voltage	V_F		0.9 1.0 1.1 1.25	V V V V	I_F=1.0mA I_F=10mA I_F=50mA I_F=150mA
Reverse Breakdown Voltage	$V_{(BR)}$	75	—	Vdc	I_{BR} = 100 uAdc
Reverse Voltage Leakage Current	I_R		5.0 80	uA nA	V_R=75V V_R=75V Tj=150℃
Capacitance	Cj		2.0	PF	V_R=0 f=1.0MHz
Reverse Recovery Time	Trr		3.0	uS	I_F=10mA to I_R=10mA

Note:Diode On Ceramic Substrate 10mm x 8.0mm x 0.7mm

DEVICE MARKING:

BAS116LT1=JV